



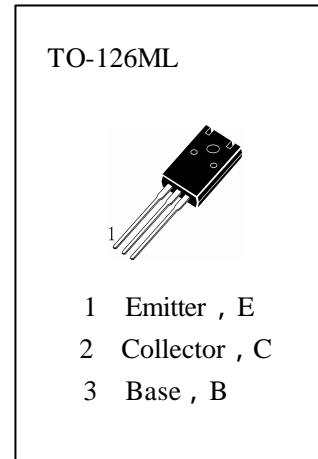
H772

APPLICATIONS

Audio Frequency Power Amplifier , Switching Power Amplifier.

ABSOLUTE MAXIMUM RATINGS ($T_a=25$)

- T_{stg} —Storage Temperature..... -55~150
- T_j —Junction Temperature..... 150
- P_C —Collector Dissipation ($T_c=25$) 10W
- P_C —Collector Dissipation ($T_A=25$) 1W
- V_{CBO} —Collector-Base Voltage..... -40V
- V_{CEO} —Collector-Emitter Voltage..... -30V
- V_{EBO} —Emitter-Base Voltage..... -5V
- I_C —Collector Current (DC)-3A
- I_b —Base Current (DC)-0.6A



ELECTRICAL CHARACTERISTICS ($T_a=25$)

Symbol	Parameter	Min	Typ	Max	Unit	Test Conditions
I_{CBO}	Collector-Base Cutoff Current			-1	μA	$V_{CB}=-30V, I_E=0$
I_{EBO}	Emitter- Base Cutoff Current			-1	μA	$V_{EB}=-5V, I_C=0$
h_{FE}	DC Current Gain	60		400		$V_{CE}=-2V, I_C=-1A$
$V_{CE(sat)}$	Collector- Emitter Saturation Voltage		-0.3	-0.5	V	$I_C=-2A, I_B=-0.2A$
$V_{BE(sat)}$	Base -Emitter Saturation Voltage		-1.0	-2.0	V	$I_C=-2A, I_B=-0.2A$
C_{ob}	Output Capacitance		55		pF	$V_{CB}=-10V, I_E=0, f=1MHz$
f_T	Current Gain-Bandwidth Product		80		MHz	$V_{CE}=-5V, I_E=-0.1A$

h_{FE} Classification

R	O	Y	G
60—120	100—200	160—320	200—400

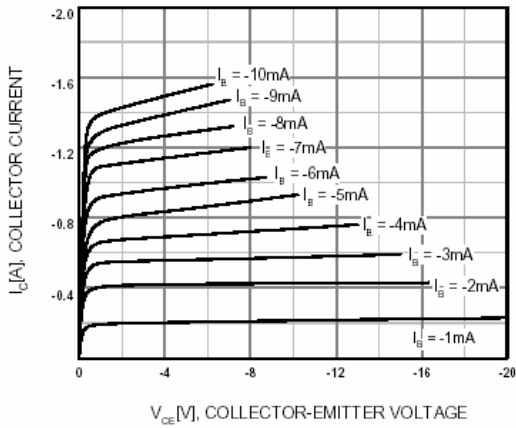


Figure 1. Static Characteristic

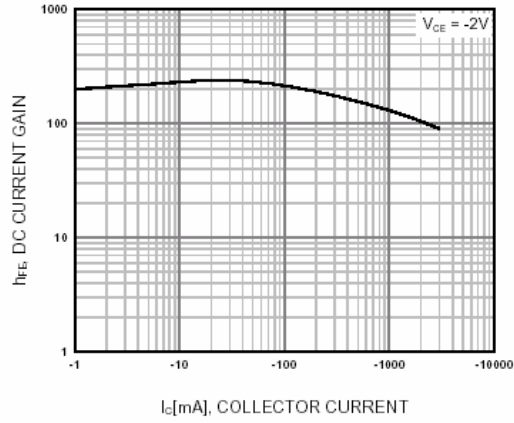


Figure 2. DC current Gain

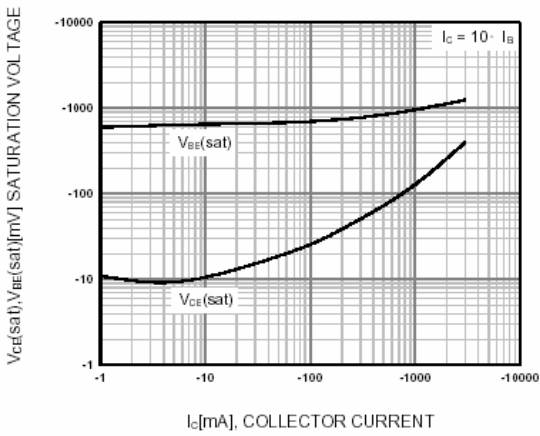


Figure 3. Base-Emitter Saturation Voltage
Collector-Emmitter Saturation Voltage

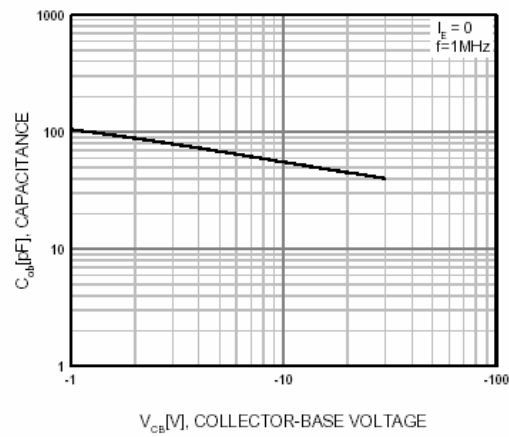


Figure 4. Collector Output Capacitance

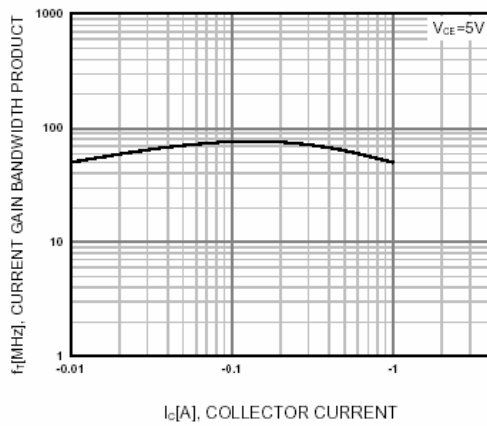


Figure 5. Current Gain Bandwidth Product

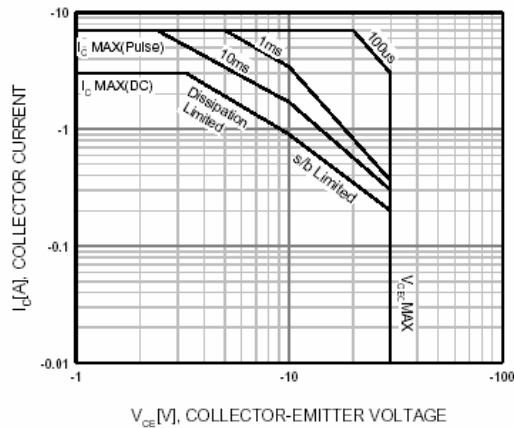


Figure 6. Safe Operating Area



Shantou Huashan Electronic Devices Co., Ltd.

PNP SILICON TRANSISTOR

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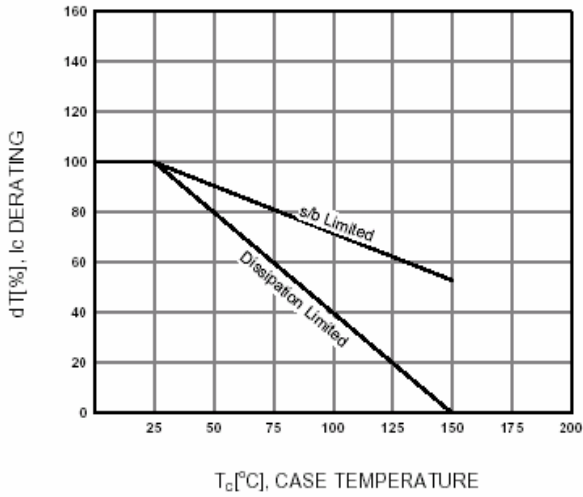


Figure 7. Derating Curve of Safe Operating Areas

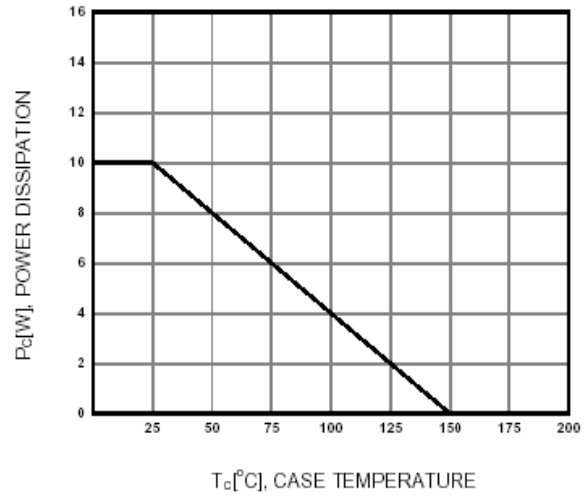


Figure 8. Power Derating